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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	25
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l041k6u6d

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Figure 44. Figure 45. Figure 46.	UFQFPN28 recommended footprint
	package outline
Figure 47.	WLCSP25 - 2.097 x 2.493 mm, 0.400 mm pitch wafer level chip scale
	recommended footprint
Figure 48.	Example of WLCSP25 marking (package top view)
Figure 49.	TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch,
	package outline
Figure 50.	TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch,
	package footprint
Figure 51.	Example of TSSOP20 marking (package top view) 113
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Peripheral	STM32 L041F4	STM32 L041G4	STM32 L041K4	STM32 L041C4	STM32 L041F6	STM32 L041E6	STM32 L041G6	STM32 L041K6	STM32 L041C6
Operating temperatures	Ambient temperature: -40 to +125 °C Junction temperature: -40 to +130 °C								
Packages	TSSOP 20	UFQFPN 28	LQFP32, UFQFPN 32	LQFP48	TSSOP 20	WLCSP 25	UFQFPN 28	LQFP32, UFQFPN 32	LQFP48

 Table 2. Ultra-low-power STM32L041x4/x6 device features and peripheral counts (continued)

1. 1 SPI interface is a USART operating in SPI master mode.

2. 23 GPIOs are available only on STM32L041GxUxS part number.

3. LQFP32 has two GPIOs, less than UFQFPN32 (27).

4. HSE external quartz connexion available only on LQFP48.

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(if internal reference voltage is on), it can be the RTC alarm/tamper/timestamp/wakeup events, the USART/I2C/LPUART/LPTIMER wakeup events.

• Stop mode without RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 μ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USART/I2C/LPUART/LPTIMER wakeup events.

• Standby mode with RTC

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

• Standby mode without RTC

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.



Operating power supply	Functionalities depending on the operating power supply range						
range	ADC operation	Dynamic voltage scaling range	I/O operation				
V _{DD} = 1.65 to 1.71 V	Conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance				
V _{DD} = 1.71 to 2.0 V ⁽¹⁾	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance				
V _{DD} = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation				
V _{DD} = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation				

 CPU frequency changes from initial to final must respect the condition: f_{CPU initial} <4f_{CPU initial}. It must also respect 5 µs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5 µs, then switch from 16 MHz to 32 MHz.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

Table 5. Functionalities depending on the working mode(from Run/active down to standby) ⁽¹⁾

			Low-	Low-		Stop	Standby	
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
CPU	Y		Y					
Flash memory	0	0	0	0				
RAM	Y	Y	Y	Y	Y			
Backup registers	Y	Y	Y	Y	Y		Y	
EEPROM	0	0	0	0				
Brown-out reset (BOR)	0	О	0	0	0	0	0	0
DMA	0	0	0	0				
Programmable Voltage Detector (PVD)	0	0	О	0	0	0	-	



The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.4 Reset and supply management

3.4.1 Power supply schemes

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.

3.4.2 Power supply supervisor

The devices feature an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.



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3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 38 GPIOs can be connected to the 16 configurable interrupt/event lines. The 10 other lines are connected to PVD, RTC, USART, I2C, LPUART, LPTIMER or comparator events.



3.15 Timers and watchdogs

The ultra-low-power STM32L041x4/6 devices include three general-purpose timers, one low- power timer (LPTM), two watchdog timers and the SysTick timer.

Table 9 compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No

Table 9. Timer feature compariso	วท
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3.15.1 General-purpose timers (TIM2, TIM21 and TIM22)

There are three synchronizable general-purpose timers embedded in the STM32L041x4/6 devices (see *Table 9* for differences).

TIM2

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 and TIM22 generalpurpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together and be synchronized with the TIM2, full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.



		Pir	n num	ber								
TSSOP20	WLCSP25	UFQFPN28	UFQFPN28 (STM32L041GxUxS only)	LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	2	PC13- ANTI_TAMP	I/O	FT	-	-	TAMP1/WKUP2
2	B5	2	2	2	2	3	PC14- OSC32_IN	I/O	тс	-	-	OSC32_IN
3	C5	3	3	3	3	4	PC15- OSC32_OUT	I/O	тс	-	-	OSC32_OUT
-	-	-	-	-	-	5	PH0-OSC_IN	I/O	тс	-	-	-
-	-	-	-	-	-	6	PH1- OSC_OUT	I/O	тс	-	-	-
4	D5	4	4	4	4	7	NRST	I/O	-	-	-	-
-	-	-	-	-	-	1	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT, LPUART1_RX	-
-	E1	-	-	-	"0"	8	VSSA	S	-	-	-	-
5	C4	5	5	5	5	9	VDDA	S	-	-	-	-
6	E5	6	6	6	6	-	PA0-CK_IN	I/O	тс	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1
-	-	-	-	-	-	10	PA0	I/O	тс	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1



Table 1	5. Pin	definitions	(continued)

		Pir	n num	ber								
TSSOP20	WLCSP25	UFQFPN28	UFQFPN28 (STM32L041GxUxS only)	LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	35	VSS	S	-	-	-	-
-	D1	-	-	-	-	36	VDD	S	-	-	-	-
20	A2	22	22	24	24	37	PA14	I/O	FT	-	SWCLK, LPTIM1_OUT, I2C1_SMBA, USART2_TX, LPUART1_TX	-
-	_	23	23	25	25	38	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	
I	B2	24	24	26	26	39	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INN
-	-	-	25	27	27	40	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT, TIM22_CH1	COMP2_INP
-	-	-	26	28	28	41	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2	COMP2_INP
-	A3	25	27	29	29	42	PB6	I/O	FTf	-	USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM21_CH1	COMP2_INP
-	A4	26	28	30	30	43	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2	COMP2_INP, VREF_PVD_IN



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 17: Voltage characteristics*, *Table 18: Current characteristics*, and *Table 19: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Max	Unit	
$V_{DD} - V_{SS}$	External main supply voltage (including V _{DDA} , V _{DD}) ⁽¹⁾	-0.3	4.0		
	Input voltage on FT and FTf pins	V _{SS} –0.3	V _{DD} +4.0		
V(2)	Input voltage on TC pins	V _{SS} –0.3	4.0	V	
VIN` ´	Input voltage on BOOT0	V_{SS}	V _{DD} +4.0		
	Input voltage on any other pin	V _{SS} –0.3	4.0		
$ \Delta V_{DD} $	Variations between different V_{DDx} power pins	-	50		
V _{DDA} -V _{DDx}	Variations between any V_{DDx} and V_{DDA} power $\mbox{pins}^{(3)}$	-	300	mV	
$ \Delta V_{SS} $	Variations between all different ground pins	-	50		
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.11			

Table 17. Voltage ch	aracteristics
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1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table 18* for maximum allowed injected current values.

3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation.







Symbol	Parameter		Conditions		Тур	Max ⁽¹⁾	Unit
			MSI clock, 65 kHz f _{HCLK} = 32 kHz Flash memory OFF	$T_A = -40 \text{ °C to } 25 \text{ °C}$	to 25 °C 3.2 ⁽²⁾ -		
			MSI clock, 65 kHz f _{HCLK} = 32 kHz Flash memory ON	T_A = -40 °C to 25 °C	13	19	
		All peripherals off, V _{DD} from 1.65 V to 3.6 V		T _A = 85 °C	16	21	μA
				T _A = 105 °C	18.5	24	
	Supply current in Low-power sleep mode			T _A = 125 °C	23.5	32	
			MSI clock, 65 kHz f _{HCLK} = 65 kHz, Flash memory ON	T_A = -40 °C to 25 °C	13.5	19	
IDD (LP Sleep)				T _A = 85 °C	16.5	21	
				T _A = 105 °C	18.5	24	
				T _A = 125 °C	24	33	
				T_A = -40 °C to 25 °C	15.5	21	
			MSI clock, 131 kHz	T _A = 55 °C	17.5	22	
			$f_{HCLK} = 131 \text{ kHz},$	T _A = 85 °C	18.5	23	
			Flash memory ON	T _A = 105 °C	21	26	
				T _A = 125 °C	26	35	

Table 30. Current consumption in Low-power Sleep mode

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

 As the CPU is in Sleep mode, the difference between the current consumption with Flash memory ON and OFF (nearly 12 μA) is the same whatever the clock frequency.



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator (LQFP48 package only). All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	1		25	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
G _m	Maximum critical crystal transconductance	Startup	-	-	700	μΑ /V
t _{SU(HSE)}	Startup time	V_{DD} is stabilized	-	2	-	ms

Table 39. HSE oscillator characteristics⁽¹⁾

1. Guaranteed by design.

2. Guaranteed by characterization results. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 22*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



Figure 22. HSE oscillator circuit diagram



Low-speed internal (LSI) RC oscillator

Table 42. LSI oscillator characteristic

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽¹⁾	LSI frequency	26	38	56	kHz
D _{LSI} ⁽²⁾	LSI oscillator frequency drift 0°C ≤T _A ≤85°C	-10	-	4	%
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	-	200	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.

2. This is a deviation for an individual part, once the initial frequency has been measured.

3. Guaranteed by design.

Multi-speed internal (MSI) RC oscillator

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	65.5	-	kH7
		MSI range 1	131	-	
		MSI range 2	262	-	KI IZ
f _{MSI}	Frequency after factory calibration, done at V_{DD} = 3.3 V and T ₄ = 25 °C	MSI range 3	524	-	
		MSI range 4	1.05	-	
		MSI range 5	2.1	-	MHz
		MSI range 6	4.2	-	
ACC _{MSI}	Frequency error after factory calibration	-	±0.5	-	%
D _{TEMP(MSI)} ⁽¹⁾	MSI oscillator frequency drift 0 °C ≤T _A <i>≤</i> 85 °C	-	±3	-	%
D _{VOLT(MSI)} ⁽¹⁾	MSI oscillator frequency drift 1.65 V ≤V _{DD} ≤3.6 V, T _A = 25 °C	-	-	2.5	%/V
		MSI range 0	0.75	-	
		MSI range 1	1	-	μA
		MSI range 2	1.5	-	
I _{DD(MSI)} ⁽²⁾	MSI oscillator power consumption	MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	

Table 43. MSI oscillator characteristics



Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	30	-	
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
+	MSL oscillator startun timo	MSI range 4	6	-	
^L SU(MSI)		MSI range 5	5	-	μs
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
		MSI range 0	-	40	μs
	MSI oscillator stabilization time	MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
to TA D (1 40) (2)		MSI range 4	-	2.5	
'STAB(MSI)		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
fourre	MSL oscillator frequency overshoot	Any range to range 5	-	4	
'OVER(MSI)	MSI oscillator frequency overshoot	Any range to range 6	-	6	11112

1. This is a deviation for an individual part, once the initial frequency has been measured.

2. Guaranteed by characterization results.

6.3.8 PLL characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Symbol	Parameter		Unit		
Symbol	Falancie	Min	Тур	Max ⁽¹⁾	Onic
f	PLL input clock ⁽²⁾	2	-	24	MHz
'PLL_IN	PLL input clock duty cycle	45	-	55	%



6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 48*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T _A = +25 °C, f _{HCLK} = 32 MHz conforms to IEC 61000-4-2	3B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3 \text{ V}, \text{LQFP48}, \text{T}_{\text{A}} = +25 \text{ °C}, \text{f}_{\text{HCLK}} = 32 \text{ MHz} \text{ conforms to IEC 61000-4-4}$	4A

Table 48. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.



Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit		
V _{DDA}	Analog supply voltage	-	1.65	-	3.6	V		
V _{IN}	Comparator 2 input voltage range	-	0	-	V_{DDA}	V		
t	Comparator startun time	Fast mode	-	15	20			
START		Slow mode	-	20	25	1		
t _{d slow}	Propagation dolay ⁽²⁾ in slow mode	1.65 V ⊴V _{DDA} ⊴2.7 V	-	1.8	3.5	μs		
	Fropagation delay in slow mode	2.7 V ≤V _{DDA} ≤3.6 V	-	2.5	6			
	Propagation delay ⁽²⁾ in fast mode	1.65 V ⊴V _{DDA} ⊴2.7 V	-	0.8	2			
^L d fast		2.7 V ≤V _{DDA} ≤3.6 V	-	1.2	4			
V _{offset}	Comparator offset error		-	±4	±20	mV		
dThreshold/ dt	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$ $T_{A} = 0 \text{ to } 50 \circ C$ $V = V_{REFINT},$ $3/4 V_{REFINT},$ $1/2 V_{REFINT},$ $1/4 V_{REFINT}.$	-	15	30	ppm /°C		
	Current consumption ⁽³⁾	Fast mode	-	3.5	5			
ICOMP2		Slow mode	-	0.5	2	- μΑ		

Table 63. Comparator 2 characteristics

1. Guaranteed by characterization results.

2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

3. Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

6.3.18 Timer characteristics

TIM timer characteristics

The parameters given in the *Table 64* are guaranteed by design.

Refer to *Section 6.3.13: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Мах	Unit
t	Timer resolution time		1	-	t _{TIMxCLK}
res(TIM)		f _{TIMxCLK} = 32 MHz	31.25	-	ns
f	Timer external clock		0	f _{TIMxCLK} /2	MHz
'EXT	frequency on CH1 to CH4	f _{TIMxCLK} = 32 MHz	0	16	MHz
Res _{TIM}	Timer resolution	-		16	bit

Table 64. TIMx⁽¹⁾ characteristics



SPI characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 20*.

Refer to Section 6.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode			16	
		Slave mode receiver	-	-	16	
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Slave mode Transmitter 1.71 <v<sub>DD<3.6V</v<sub>	-	-	12 ⁽²⁾	MHz
		Slave mode Transmitter 2.7 <v<sub>DD<3.6V</v<sub>	-	-	16 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency Slave mode		30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)} t _{w(SCKL)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data input actus timo	Master mode	8.5	-	-	
t _{su(SI)}	Data input setup time	Slave mode	8.5	-	-	
t _{h(MI)}	Data input hold time	Master mode		-	-	
t _{h(SI)}		Slave mode	1	-	-	ns
t _{a(SO}	Data output access time	Slave mode	15	-	36	
t _{dis(SO)}	Data output disable time	Slave mode	10	-	30	
t		Slave mode 1.71 <v<sub>DD<3.6V</v<sub>	-	29	41	
۷(SO)	Data output valid time	Slave mode 2.7 <v<sub>DD<3.6V</v<sub>	-	22	28	
t _{v(MO)}		Master mode	-	10	17	
t _{h(SO)}	Data output hold time	Slave mode	9	-	-	
t _{h(MO)}		Master mode	3	-	-	

Table 67. SPI characteristics	; in	voltage Range	1	(1)	
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1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{y(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
f _{SCK}	SDI alaak fraguanay	Master mode			2		
1/t _{c(SCK)}	SFI Clock frequency	Slave mode	-	-	2 ⁽²⁾		
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%	
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-		
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-		
t _{w(SCKH)} t _{w(SCKL)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2		
t _{su(MI)}	Data input actus timo	Master mode	28.5	-	-		
t _{su(SI)}	Data input setup time	Slave mode	22	-	-		
t _{h(MI)}	Data input hold time	Master mode	7	-	-		
t _{h(SI)}	Data input noid time	Slave mode	5	-	-	ns	
t _{a(SO}	Data output access time	Slave mode	30	-	70		
t _{dis(SO)}	Data output disable time	Slave mode	40	-	80		
t (ac)	Data output valid time	Slave mode	-	53	86		
⁴ ۷(SO)		Master mode	-	30	54	1	
t _{v(MO)}	Data output hold time	Slave mode	18	-	-		
t _{h(SO)}	Data output hold time	Master mode	8	-	-		

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1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.



Figure 31. SPI timing diagram - slave mode and CPHA = 0

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7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status *are available at http://www.st.com.* ECOPACK[®] is an ST trademark.

7.1 LQFP48 package information



Figure 34. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package outline

1. Drawing is not to scale.



7.5 WLCSP25 package information



Figure 46. WLCSP25 - 2.097 x 2.493 mm, 0.400 mm pitch wafer level chip scale package outline

Table 74. WLCSP25 - 2.097 x 2.493 mm, 0.400 mm pitch wafer level chip scale
mechanical data

Symbol	Milimeters			Inches ⁽¹⁾			
Cymbol	Min	Тур	Мах	Min	Тур	Мах	
А	0.5250	0.5550	0.5850	0.0207	0.0219	0.0230	
A1	-	0.1750	-	-	0.0069	-	
A2	-	0.3800	-	-	0.0150	-	
A3 ⁽²⁾	-	0.0250	-	-	0.0010	-	
b ⁽³⁾	0.2200	0.2500	0.2800	0.0087	0.0098	0.0110	
D	2.0620	2.0970	2.1320	0.0812	0.0826	0.0839	
E	2.4580	2.4930	2.5280	0.0968	0.0981	0.0995	
е	-	0.4000	-	-	0.0157	-	
e1	-	1.6000	-	-	0.0630	-	
e2	-	1.6000	-	-	0.0630	-	
F	-	0.2485	-	-	0.0098	-	
G	-	0.4465	-	-	0.0176	-	

